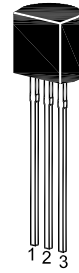


NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into six groups, D, E, F, G, H and I, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Base 3. Collector
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	50	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	30	mA
Power Dissipation	P_{tot}	400	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $V_{CE} = 5\text{ V}$, $I_C = 1\text{ mA}$ Current Gain Group	D	h_{FE}	28	-	45	-
	E	h_{FE}	39	-	60	-
	F	h_{FE}	54	-	80	-
	G	h_{FE}	72	-	108	-
	H	h_{FE}	97	-	146	-
	I	h_{FE}	132	-	198	-
Collector Base Cutoff Current at $V_{CB} = 50\text{ V}$	I_{CBO}	-	-	100	nA	
Emitter Base Cutoff Current at $V_{EB} = 5\text{ V}$	I_{EBO}	-	-	100	nA	
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CBO}$	50	-	-	V	
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	30	-	-	V	
Emitter Base Breakdown Voltage at $I_E = 100\text{ }\mu\text{A}$	$V_{(BR)EBO}$	5	-	-	V	
Collector Emitter Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 1\text{ mA}$	$V_{CE(sat)}$	-	0.08	0.3	V	
Base Emitter Voltage at $V_{CE} = 5\text{ V}$, $I_C = 1\text{ mA}$	$V_{BE(on)}$	0.60	0.7	0.75	V	
Collector Base Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{cbo}	-	1.5	-	pF	
Gain Bandwidth Product at $V_{CE} = 5\text{ V}$, $I_C = 1\text{ mA}$	f_T	150	370	-	MHz	

